

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent No.: 7,084,030
Inventor: Chang-Hyun LEE, et al.
Issued: August 1, 2006
Ser. No.: 10/632,496 Filed: July 31, 2003
Group Art Unit: 2811 Examiner: Donghee KANG
For: METHOD OF FORMING A NON-VOLATILE MEMORY DEVICE
HAVING FLOATING TRAP TYPE MEMORY CELL

REQUEST FOR CERTIFICATE OF CORRECTION

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Upon comparison of the above-identified original Letters Patent with applicant's copy of the application, the following errors, made by the USPTO, in the original Letters Patent has been noted:

Column 4, line 3, the word "substrate" should read -- substrate, --;
Column 5, line 14, the words "order This" should read -- order. This --;
Column 14, line 39, the word "region," should read -- region; --;
Column 15, line 47, the word "high-conductivitiv" should read -- high-conductivity --;
Column 15, line 57, the word "fonning" should read -- forming --;
Column 15, line 59, the word "cefl" should read -- cell --;
Column 16, line 20, the word "flurther" should read -- further --;
Column 18, line 11, the word "high-conductivitiv" should read -- high-conductivity --;
Column 18, line 13, the word "sate" should read -- gate --;
Column 18, line 25, the word "gale" should read -- gate --.

Applicant respectfully requests that a Certificate of Correction calling attention to the above error be issued pursuant to Rule 322 of the Patent Office and Title 35, United States Code, Section 254.

Respectfully submitted,
MARGER JOHNSON & McCOLLUM, P.C.



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UNITED STATES PATENT AND TRADEMARK OFFICE CERTIFICATE OF CORRECTION

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APPLICATION NO.: 10/632,496

ISSUE DATE : August 1, 2006

INVENTOR(S) : Chang-Hun LEE, et al.

It is certified that an error appears or errors appear in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

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MAILING ADDRESS OF SENDER (Please do not use customer number below):

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This collection of information is required by 37 CFR 1.322, 1.323, and 1.324. The information is required to obtain or retain a benefit by the public which is to file (and by the USPTO to process) an application. Confidentiality is governed by 35 U.S.C. 122 and 37 CFR 1.14. This collection is estimated to take 1.0 hour to complete, including gathering, preparing, and submitting the completed application form to the USPTO. Time will vary depending upon the individual case. Any comments on the amount of time you require to complete this form and/or suggestions for reducing this burden, should be sent to the Chief Information Officer, U.S. Patent and Trademark Office, U.S. Department of Commerce, P.O. Box 1450, Alexandria, VA 22313-1450. DO NOT SEND FEES OR COMPLETED FORMS TO THIS ADDRESS. SEND TO: **Attention Certificate of Corrections Branch, Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450.**

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